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SI4532CDY

N/P-Channel Enhancement Mode Power MOSFET

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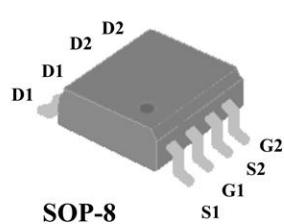
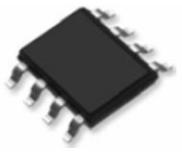
GENERAL FEATURES

N-CH	BV_{DSS}	30V
	$R_{DS(ON)}$	22mΩ
	I_D	7A
P-CH	BV_{DSS}	-30V
	$R_{DS(ON)}$	30mΩ
	I_D	-6.0A

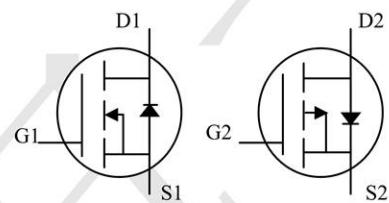
Application

- Battery protection
- Load switch

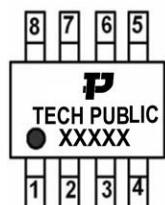
Package and Pin Configuration



Circuit diagram



Marking:



“P” is TECHPUBLIC LOGO

“XXXXX” Marking ID (Please see the last page for details)

Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise noted)

PARAMETER	SYMBOL	N-CH LIMIT	P-CH LIMIT	UNITS
Drain-Source Voltage	V_{DS}	30	-30	V
Gate-Source Voltage	V_{GS}	± 20		
Continuous Drain Current <small>(Note 4)</small>	$T_A=25^\circ\text{C}$	I_D	7	A
	$T_A=70^\circ\text{C}$		5.6	
Pulsed Drain Current <small>(Note 1)</small>	$T_C=25^\circ\text{C}$	I_{DM}	28	-24
Power Dissipation	$T_A=25^\circ\text{C}$	P_D	1.7	W
	$T_A=70^\circ\text{C}$		1.1	
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55~150		°C
Typical Thermal Resistance Junction to Ambient <small>(Note 4,5)</small>	$R_{\theta JA}$	73.5		°C/W



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N-CH Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=250\mu\text{A}$	30	-	-	V
Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=250\mu\text{A}$	1	1.67	2.5	
Drain-Source On-State Resistance	$R_{\text{DS}(\text{on})}$	$V_{\text{GS}}=10\text{V}, I_{\text{D}}=6\text{A}$	-		22	$\text{m}\Omega$
Drain-Source On-State Resistance	$R_{\text{DS}(\text{on})}$	$V_{\text{GS}}=4.5\text{V}, I_{\text{D}}=3\text{A}$	-		28	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{\text{DS}}=30\text{V}, V_{\text{GS}}=0\text{V}$	-	-	1	μA
Gate-Source Leakage Current	I_{GSS}	$V_{\text{GS}}=\pm 20\text{V}, V_{\text{DS}}=0\text{V}$	-	-	± 100	nA
Dynamic <small>(Note 6)</small>						
Total Gate Charge	Q_g	$V_{\text{DS}}=15\text{V}, I_{\text{D}}=8\text{A},$ $V_{\text{GS}}=4.5\text{V}$ <small>(Note 2,3)</small>	-	4.8	-	nC
Gate-Source Charge	Q_{gs}		-	1.5	-	
Gate-Drain Charge	Q_{gd}		-	2	-	
Input Capacitance	C_{iss}	$V_{\text{DS}}=25\text{V}, V_{\text{GS}}=0\text{V},$ $f=1\text{MHZ}$	-	429	-	pF
Output Capacitance	C_{oss}		-	59	-	
Reverse Transfer Capacitance	C_{rss}		-	47	-	
Turn-On Delay Time	$t_{\text{d}(\text{on})}$	$V_{\text{DS}}=15\text{V}, I_{\text{D}}=1\text{A},$ $V_{\text{GS}}=10\text{V}, R_{\text{G}}=6\Omega$ <small>(Note 2,3)</small>	-	6.8	-	ns
Turn-On Rise Time	t_r		-	16	-	
Turn-Off Delay Time	$t_{\text{d}(\text{off})}$		-	27	-	
Turn-Off Fall Time	t_f		-	7.1	-	
Drain-Source Diode						
Maximum Continuous Drain-Source Diode Forward Current	I_s	---	-	-	7	A
Diode Forward Voltage	V_{SD}	$I_s=1\text{A}, V_{\text{GS}}=0\text{V}$	-	0.74	1	V



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PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=-250\mu A$	-30	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1	-1.53	-2.5	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=-10V, I_D=-4A$	-		30	$m\Omega$
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=-4.5V, I_D=-2A$	-		45	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-30V, V_{GS}=0V$	-	-	-1	μA
Gate-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
Dynamic (Note 6)						
Total Gate Charge	Q_g	$V_{DS}=-15V, I_D=-4A,$ $V_{GS}=-4.5V$ (Note 1,2)	-	7.8	-	nC
Gate-Source Charge	Q_{gs}		-	2.7	-	
Gate-Drain Charge	Q_{gd}		-	2.8	-	
Input Capacitance	C_{iss}	$V_{DS}=-15V, V_{GS}=0V,$ $f=1MHz$	-	846	-	pF
Output Capacitance	C_{oss}		-	120	-	
Reverse Transfer Capacitance	C_{rss}		-	76	-	
Turn-On Delay Time	$t_{d(on)}$	$V_{DS}=-15V, I_D=-1A,$ $V_{GS}=-10V, R_G=6\Omega$ (Note 1,2)	-	3.6	-	ns
Turn-On Rise Time	t_r		-	23	-	
Turn-Off Delay Time	$t_{d(off)}$		-	90	-	
Turn-Off Fall Time	t_f		-	50	-	
Drain-Source Diode						
Maximum Continuous Drain-Source Diode Forward Current	I_S	---	-	-	-6	A
Diode Forward Voltage	V_{SD}	$I_S=-1A, V_{GS}=0V$	-	-0.75	-1	V

Typical Electrical and Thermal Characteristics (Curves)

N-Channel Typical Operating Characteristics

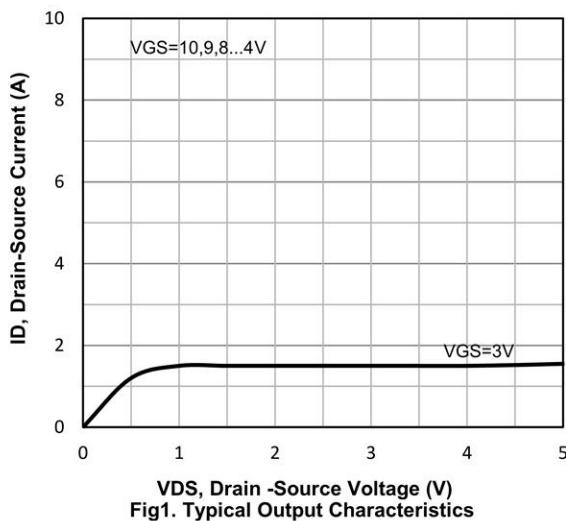


Fig1. Typical Output Characteristics

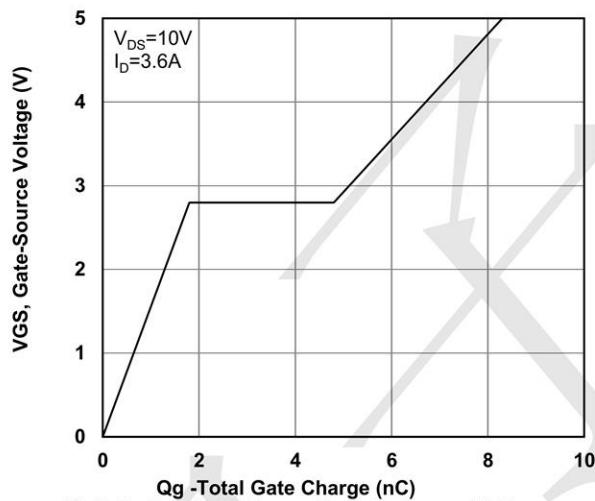


Fig2. Typical Gate Charge Vs.Gate-Source Voltage

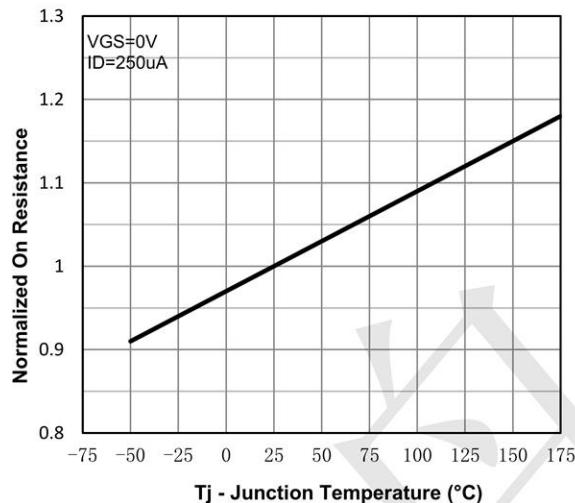


Fig3. Normalized On-Resistance Vs. Temperature

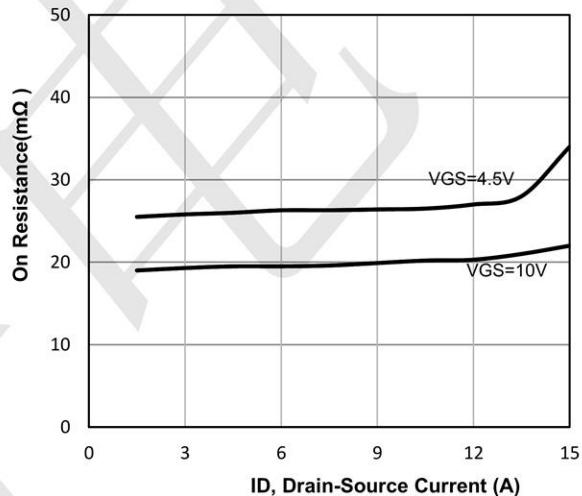


Fig4. On-Resistance Vs. Drain-Source Current

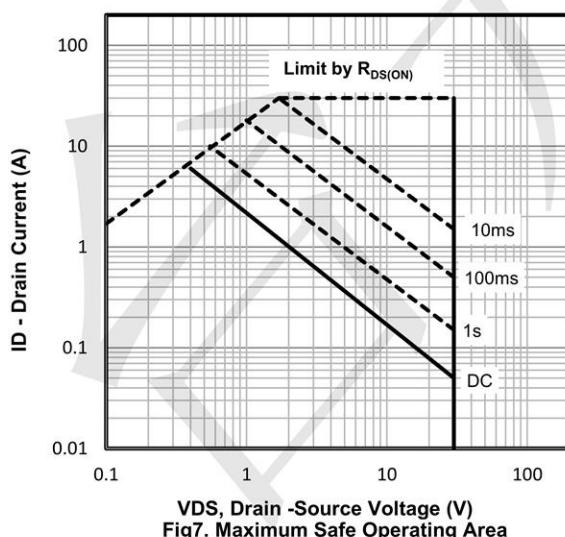


Fig7. Maximum Safe Operating Area

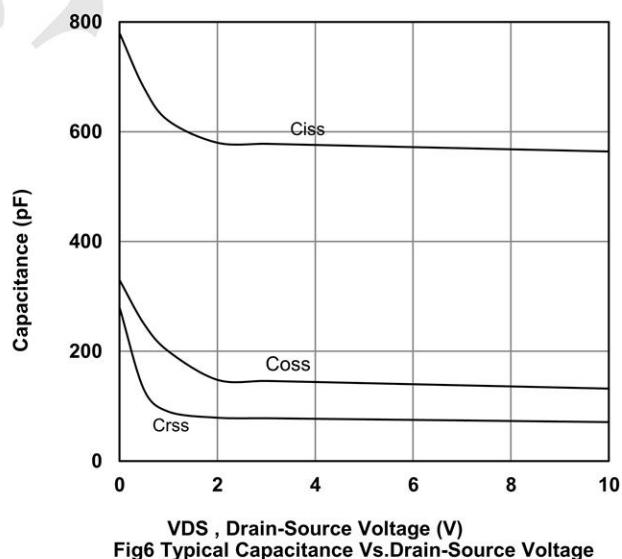


Fig6 Typical Capacitance Vs.Drain-Source Voltage

P-Channel Typical Operating Characteristics

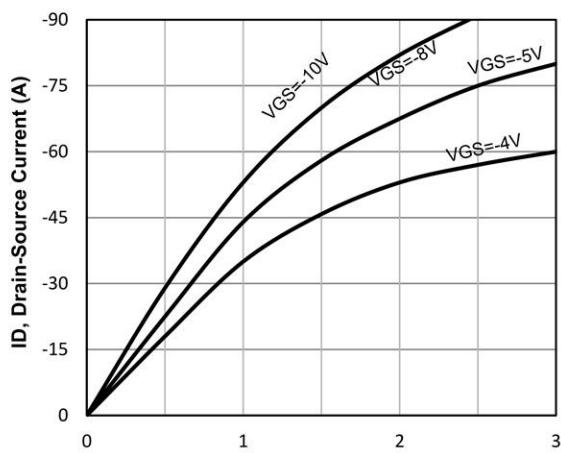


Fig1. Typical Output Characteristics

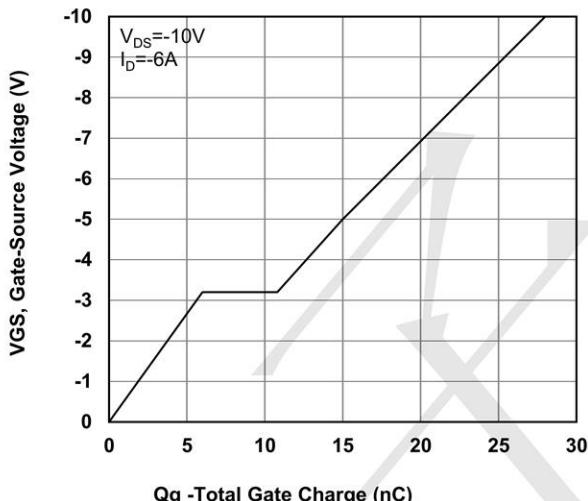


Fig2. Typical Gate Charge Vs.Gate-Source Voltage

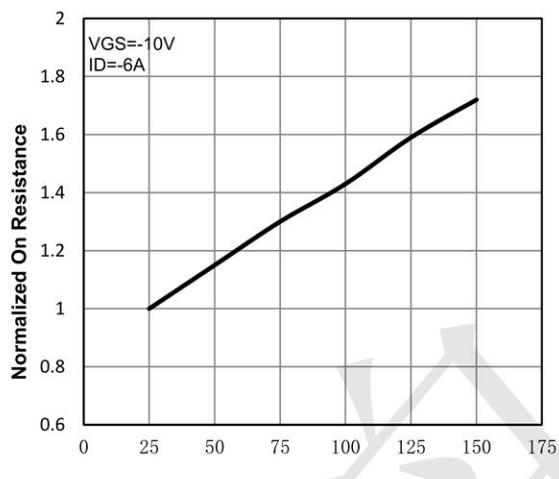


Fig3. Normalized On-Resistance Vs. Temperature

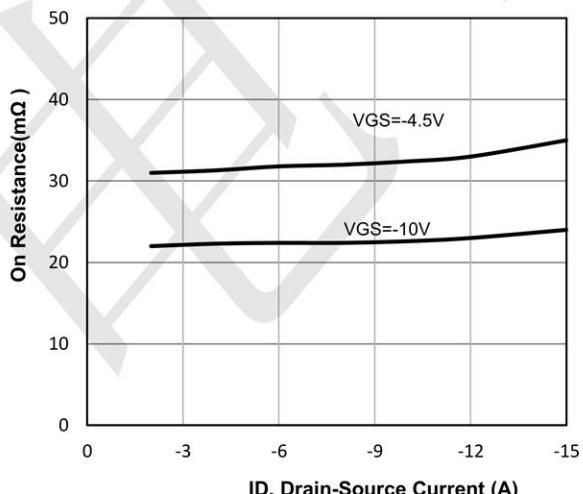


Fig4. On-Resistance Vs. Drain-Source Current

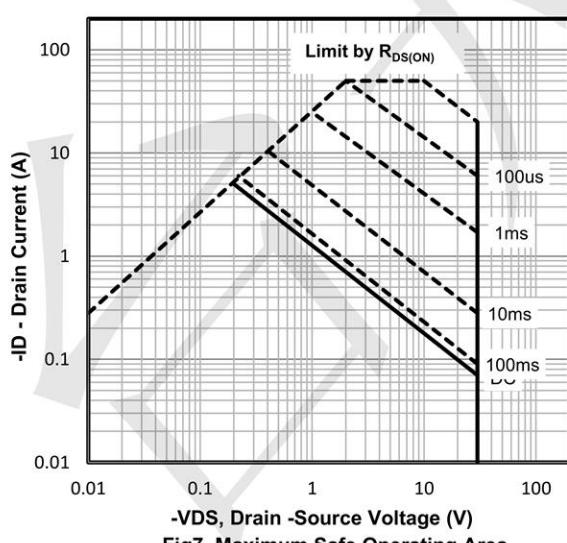


Fig7. Maximum Safe Operating Area

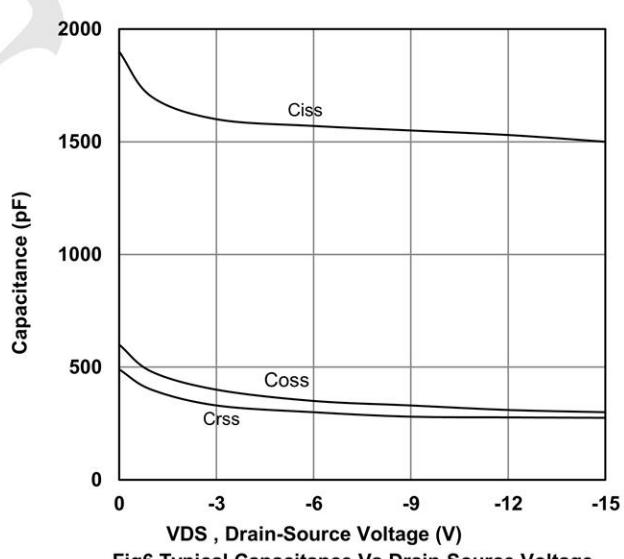


Fig6. Typical Capacitance Vs.Drain-Source Voltage



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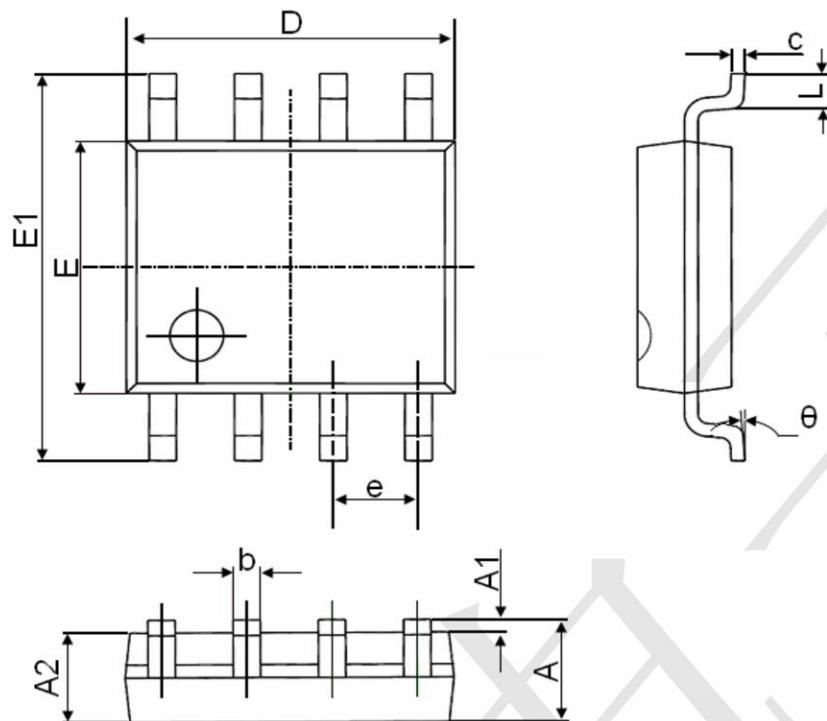
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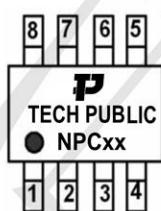
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SOP-8 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°

Marking:



“P” is TECHPUBLIC LOGO

“NPC” is Part number,fixed

“xx” is internal code

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